LIGHT EMITTING DEVICE

ABSTRACT OF THE DISCLOSURE

A light emitting device includes a nitride semiconductor substrate (1) with a resistivity of 0.5 Ω·cm or less, an n-type nitride semiconductor layer (3) and a p-type nitride semiconductor layer (5) placed more distantly from the nitride semiconductor substrate (1) than the n-type nitride semiconductor layer at a first main surface side of the nitride semiconductor substrate (1), and a light emitting layer (4) placed between the n-type nitride semiconductor layer (3) and the p-type nitride semiconductor layer (5), wherein one of the nitride semiconductor substrate (1) and the p-type nitride semiconductor layer (5) is mounted at the top side which emits light and the other is placed at the down side, and a single electrode is placed at the top side. Therefore, there is provided a light emitting device which has a simple configuration thereby making it easy to fabricate, can provide a high light emission efficiency for a long time period, and can be easily miniaturized.

Figure 2